# **CPC** COOPERATIVE PATENT CLASSIFICATION

## H ELECTRICITY

(NOTE omitted)

## H03 ELECTRONIC CIRCUITRY

### **H03C** MODULATION (masers or lasers <u>H01S</u>; coding, decoding or code conversion <u>H03M</u>)

#### **NOTES**

- 1. This subclass <u>covers</u> only modulation, keying, or interruption of sinusoidal oscillations or electromagnetic waves, the modulating signal having any desired waveform.
- 2. In this subclass, circuits usable both as modulator and demodulator are classified in the group dealing with the type of modulator involved.

#### WARNING

The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following<br/>CPC groups:H03C 1/38 - H03C 1/44covered byH03C 1/36

1/00	Amplitude modulation (H03C 5/00, H03C 7/00 take
	precedence)
1/02	• Details
1/04	Means in or combined with modulating stage for
	reducing angle modulation
1/06	Modifications of modulator to reduce distortion,
	e.g. by feedback, and clearly applicable to more
	than one type of modulator
1/08	• by means of variable impedance element
	( <u>H03C 1/28</u> - <u>H03C 1/34</u> , <u>H03C 1/46</u> - <u>H03C 1/52</u> ,
1/10	<u>H03C 1/62</u> take precedence)
1/10	• the element being a current-dependent inductor
1/12 1/14	• the element being a voltage-dependent capacitor
	• the element being a diode
1/16	• by means of discharge device having at least three electrodes ( <u>H03C 1/28</u> - <u>H03C 1/34</u> , <u>H03C 1/50</u> ,
	<u>H03C 1/52, H03C 1/62</u> take precedence)
1/18	carrier applied to control grid
1/20	• • • modulating signal applied to anode
1/22	• • • modulating signal applied to same grid
1/24	modulating signal applied to different grid
1/26	modulating signal applied to cathode
1/28	• by means of transit-time tube
1/30	• • by means of a magnetron
1/32	• by deflection of electron beam in discharge tube
1/34	• by means of light-sensitive element
1/36	• by means of semiconductor device having at
	least three electrodes (H03C 1/34, H03C 1/50,
	H03C 1/52, H03C 1/62 take precedence)
1/46	• Modulators with mechanically-driven or
	acoustically-driven parts
1/48	. by means of Hall-effect devices
1/50	• by converting angle modulation to amplitude
	modulation ( <u>H03C 1/28</u> - <u>H03C 1/34</u> , <u>H03C 1/46</u> , H03C 1/48 take presedence)
1/52	H03C 1/48 take precedence) Modulators in which carrier or one
1/52	sideband is wholly or partially suppressed
	( <u>H03C 1/28</u> - <u>H03C 1/34</u> , <u>H03C 1/46</u> , <u>H03C 1/48</u>
	take precedence)

1/54	• Balanced modulators, e.g. bridge type, ring type or double balanced type
1/542	• • {comprising semiconductor devices with at least three electrodes}
1/545	• • • • {using bipolar transistors}
1/547	• • • • {using field-effect transistors}
1/56	comprising variable two-pole elements only
1/58	comprising diodes
1/60	with one sideband wholly or partially suppressed
1/62	. Modulators in which amplitude of carrier
	component in output is dependent upon
	strength of modulating signal, e.g. no carrier
	output when no modulating signal is present
	( <u>H03C 1/28</u> - <u>H03C 1/34</u> , <u>H03C 1/46</u> , <u>H03C 1/48</u> take precedence)
3/00	Angle modulation ( <u>H03C 5/00</u> , <u>H03C 7/00</u> take
5/00	precedence)
3/005	• {Circuits for asymmetric modulation}
3/02	• Details
3/04	Means in or combined with modulating stage for
	reducing amplitude modulation
3/06	Means for changing frequency deviation
3/08	Modifications of modulator to linearise
	modulation, e.g. by feedback, and clearly
	applicable to more than one type of modulator
3/09	Modifications of modulator for regulating the mean frequency
3/0908	• • • {using a phase locked loop}
3/0916	• • • • { with frequency divider or counter in the
	loop}
3/0925	• • • • {applying frequency modulation at the
2/0022	divider in the feedback loop}
3/0933	• • • • {using fractional frequency division in the feedback loop of the phase locked loop}
3/0941	• • • { applying frequency modulation at more than one point in the loop }
3/095	• • • • {applying frequency modulation to the loop
	in front of the voltage controlled oscillator}

### H03C

3/0958	•••• {applying frequency modulation by varying
	the characteristics of the voltage controlled oscillator}
3/0966	• • • {modulating the reference clock}
3/0975	• • • • {applying frequency modulation in the phase
	locked loop at components other than the
	divider, the voltage controlled oscillator or
	the reference clock}
3/0983	• • • {containing in the loop a mixer other than for
	phase detection }
3/0991	{including calibration means or calibration
2/10	methods }
3/10	• by means of variable impedance $(102C_{2}^{2}/20_{2}) = 102C_{2}^{2}/20_{2}$ take space dense)
2/10	$(\underline{H03C 3/30} - \underline{H03C 3/38}$ take precedence)
3/12	• by means of a variable reactive element
3/14	simulated by circuit comprising active element
	with at least three electrodes, e.g. reactance- tube circuit
3/145	• • • {by using semiconductor elements}
3/145	• • • • • • • • • • • • • • • • • • •
5/10	serves as the active element of an oscillator
3/18	• • • the element being a current-dependent inductor
3/20	the element being a voltage-dependent
5/20	capacitor
3/22	• • • the element being a semiconductor diode, e.g.
	varicap diode
3/222	• • • • {using bipolar transistors ( <u>H03C 3/227</u> takes
	precedence)}
3/225	• • • • {using field effect transistors ( <u>H03C 3/227</u>
	takes precedence)}
3/227	• • • { using a combination of bipolar transistors
	and field effect transistors}
3/24	• • by means of a variable resistive element, e.g. tube
3/245	• • • {by using semiconductor elements}
3/26	comprising two elements controlled in push-
2/20	pull by modulating signal
3/28	• using variable impedance driven mechanically or
3/30	acoustically by means of transit-time tube
3/30	5
3/32 3/34	<ul><li>the tube being a magnetron</li><li>by deflection of electron beam in discharge tube</li></ul>
3/34 3/36	
3/38	<ul><li> by means of light-sensitive element</li><li> by converting amplitude modulation to angle</li></ul>
3/30	modulation
3/40	• using two signal paths the outputs of which have
5/40	a predetermined phase difference and at least one
	output being amplitude-modulated
3/403	• • • {using two quadrature frequency conversion
	stages in cascade}
3/406	• • • {using a feedback loop containing mixers or
	demodulators }
3/42	• by means of electromechanical devices (H03C 3/28
	takes precedence)
5/00	Amplitude modulation and angle modulation
5/00	produced simultaneously or at will by the same
	modulating signal ( <u>H03C 7/00</u> takes precedence)
5/02	• by means of transit-time tube
5/04	• • the tube being a magnetron
5/06	<ul> <li>by deflection of electron beam in discharge tube</li> </ul>
7/00	<b>Modulating electromagnetic waves</b> (devices or arrangements for the modulation of light CO2E 1/00)
7/02	arrangements for the modulation of light <u>G02F 1/00</u> )
1/02	<ul> <li>in transmission lines, waveguides, cavity resonators or radiation fields of antennas</li> </ul>
	or radiation news of antennas

7/022 7/025 7/027 7/04	<ul> <li>{using ferromagnetic devices, e.g. ferrites}</li> <li>{using semiconductor devices}</li> <li>{using diodes}</li> <li>Polarisation of transmitted wave being modulated</li> </ul>
99/00	{( <u>H03C 7/022</u> takes precedence)} Subject matter not provided for in other groups of this subclass
2200/00	Indexing scheme relating to details of modulators
	or modulation methods covered by <u>H03C</u>
2200/0004	Circuit elements of modulators
2200/0008	• Variable capacitors, e.g. a varicap, a varactor or a variable capacitance of a diode or transistor
2200/0012	Emitter or source coupled transistor pairs or long tail pairs
2200/0016	• Pre-emphasis or de-emphasis circuits
2200/0010	Filters with particular characteristics
2200/0025	Gilbert multipliers
2200/0029	• Memory circuits, e.g. ROMs, RAMs, EPROMs,
	latches, shift registers
2200/0033	Transmission lines, e.g. striplines, microstrips or coplanar lines
2200/0037	• Functional aspects of modulators
2200/0041	Calibration of modulators
2200/0045	• • Pulse width, duty cycle or on/off ratio
2200/005	• • Modulation sensitivity
2200/0054	••• Filtering of the input modulating signal for
	obtaining a constant sensitivity of frequency modulation
2200/0058	• • Quadrature arrangements
2200/0062	• • Lowering the supply voltage and saving power
2200/0066	• Reduction of carrier leakage or the suppression of the carrier
2200/007	with one sideband wholly or partially suppressed
2200/0075	• • FM modulation down to DC
2200/0079	Measures to linearise modulation or reduce distortion of modulation characteristics
2200/0083	• • Predistortion of input modulating signal to obtain a linear modulation characteristic
2200/0087	Measures to address temperature induced variations of modulation
2200/0091	• • • by stabilising the temperature
2200/0095	by compensating the temperature induced
	variations